

Application No.: 09/580,485
Art Unit: 2813

Attorney Docket No.: 740756-2154
Page 2

forming a second insulating film comprising silicon nitride on the first insulating film;

forming a pixel electrode on the second insulating film, said pixel electrode electrically connected to the thin film transistor;

forming an EL layer over the pixel electrode;

forming a second electrode over the EL layer,

wherein the EL layer is selectively formed through an ink jet method.